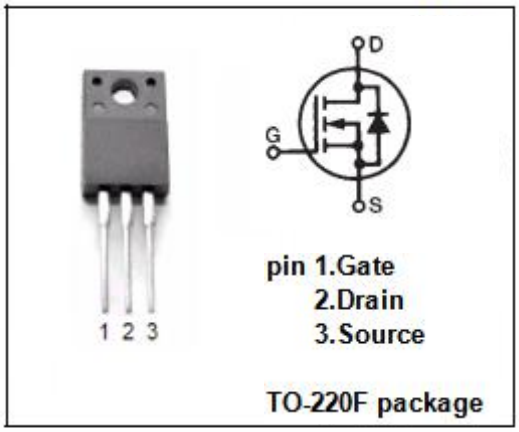
isc N-Channel MOSFET Transistor FDPF680N10T

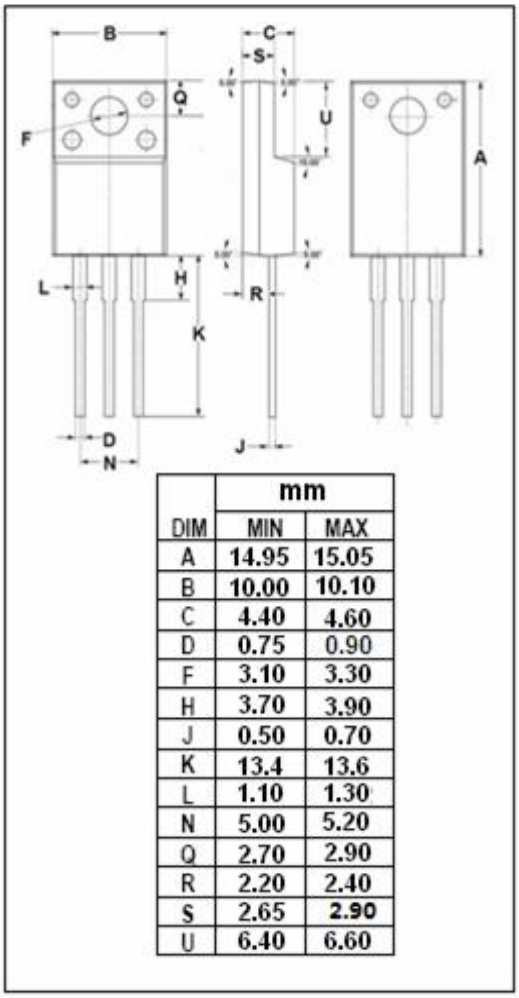
- **FEATURES**
- With TO-220F packaging
- Drain Source Voltage-
  : V_{DSS} ≥ 100V
- Static drain-source on-resistance:
  R_{DS}(on) ≤ 68mΩ@V_{GS}=10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **APPLICATIONS**
- Power supply
- Switching applications

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous;@Tc=25℃	12	A
I_{DM}	Drain Current-Single Pulsed	48	A
P_D	Total Dissipation	24	W
T_j	Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	5.2	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 250uA	100			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=250uA	2.5		4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 6A			68	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V;V_{DS}= 0V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 100V; V_{GS}= 0V V_{DS}= 100V; V_{GS}= 0V;T_J=150℃			1 500	μA
V_{SDF}	Diode forward voltage	I_{SD}= 12A, V_{GS} = 0 V			1.3	V